

## Understanding the role of dopants in the thermoelectric properties of PbSe

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Interestingly, thermoelectricity is known to convert the waste heat into electricity. The thermoelectric efficiency is enumerated by dimensionless figure of merit (ZT), which is related to Seebeck coefficient ( $\alpha$ ), electrical conductivity ( $\sigma$ ) and thermal conductivity ( $\kappa$ ) by the relation  $ZT = (\alpha^2 \sigma / \kappa) T$  [1-2]. Widely studied PbSe has high Seebeck coefficient and the past studies suggested that, Na, K, Tl, Ag are the effective hole dominate dopants, whereas doping through Cr, Ga, In, B induce the electron concentration in PbSe, making it n-type [1-3]. In relation to this, we have synthesized PbSe: $M_x$  ( $M = \text{Al, Ni, Cu}$ ;  $x \sim 0.02$ ) via solid state synthesis. The synthesis was carried out in a vacuum-sealed quartz ampoule at 1373 K. The as-synthesized samples were polished before further analysis for thermoelectric performances.

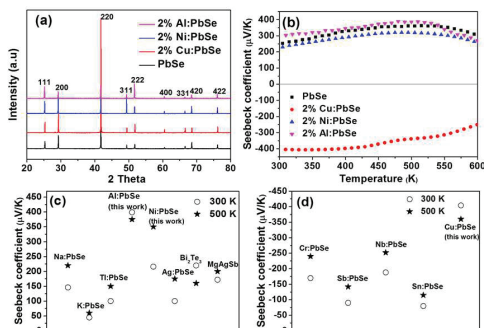


Figure 1: (a) XRD of PbSe: $M_x$  ( $M = \text{Al, Ni, Cu}$ ;  $0 \leq x \leq 0.02$ ), (b) Temperature dependence of Seebeck coefficient of PbSe: $M_x$  ( $M = \text{Al, Ni, Cu}$ ;  $0 \leq x \leq 0.02$ ), (c & d) Comparison of Seebeck coefficient with other reports

Figure 1 (a) shows the cubic rock-salt structure with most intense reflection at  $2\theta$  of  $42.2^\circ$  (for 220), having the close match with other references [JCPDS 06-0354] [3]. The  $\alpha$  of bare PbSe  $\sim 254 \mu\text{V/K}$ , PbSe:2%Al  $\sim 302 \mu\text{V/K}$ , PbSe:2%Ni  $\sim 236 \mu\text{V/K}$ , PbSe:2%Cu  $\sim 397 \mu\text{V/K}$  represents the individual role of dopants ( $\alpha_{\text{Cu}} > \alpha_{\text{Al}} > \alpha_{\text{Ni}}$ ), as can be seen in Figure 1 (b). In such case, the nature of dopant as well as the shifting of Fermi energy ( $E_f$ ) level inside the conduction/valence band conveniently impact over the Seebeck coefficient. Interestingly, the obtained Seebeck coefficient is comparatively larger than other elemental doped PbSe, as shown in Figure 1 (c and d). Furthermore, Cu acts as a donor in PbSe, while Al and Ni are acting as acceptor. A nearly linear temperature dependence of Seebeck coefficient indicates typical degenerate conduction in PbSe: $M_x$  ( $M = \text{Al, Ni}$ ;  $0 \leq x \leq 0.02$ ).

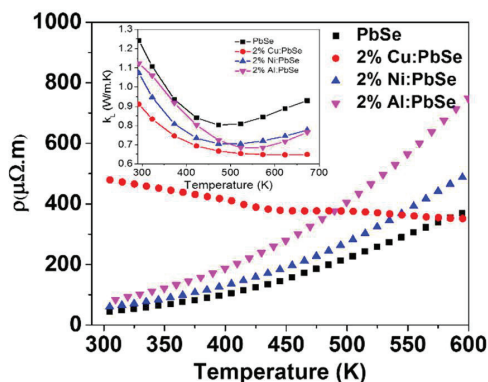


Figure 2: Temperature dependence of electrical conductivity of PbSe: $M_x$  ( $M = \text{Al, Ni, Cu}$ ;  $0 \leq x \leq 0.02$ ) (Inset figure represents lattice thermal conductivity)

The temperature dependence of resistivity is studied in Figure 2, where a monotonic rise in the resistivity with temperature indicates a typical degenerate conduction for PbSe: $M_x$  ( $M = \text{Al, Ni}$ ;  $0 \leq x \leq 0.02$ ). Additionally, the increase of resistivity at high temperature could be described with carrier-phonon interaction, as the mobility decreases with carrier-phonon scattering. Therefore, in Al/Ni doped PbSe the resistivity increases with temperature and follows the degenerate semiconductor characteristics. In fact the donor behavior of Cu dopant follows the non-degenerate characteristic and with this the decreasing trend of resistivity with temperature has been noticed. Through the alloy/point scattering the lattice thermal conductivity of doped PbSe varies as,  $\kappa_{\text{Cu}} < \kappa_{\text{Ni}} < \kappa_{\text{Al}}$ . Hence, the intrinsic nature of dopants severally influences the thermoelectric properties.

### References

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